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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,294,442	9/2001	Kamal			
	5,683,935	11/1997	Miyamoto et al.			
	5,385,863	1/1995	Tatsumi et al.			
	4,755,476	7/1988	Bohm et al.			
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	0 521 644	1/1993	EPO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Becker et al., LOW RESISTANCE POLYCRYSTALLINE SILICON BY BORON OR ARSENIC IMPLANTATION AND THERMAL CRYSTALLIZATION OF AMORPHOUSLY DEPOSITED FILMS, J. Appl. Phys., Vol. 56, No. 4, 15 August 1984, pages 1233-1236
		Carbone et al., "Correlation of Ellipsometric Vol. Fraction to Polysilicon Grain Size from Transmission Electron Microscopy", Sept. 1999, IEEE/SEMI Adv. Semiconductor Mfg. Conf. and Workshop, pp. 359-367.

EXAMINER

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